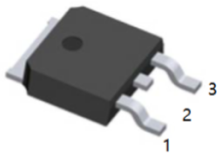
Description

This N-Channel enhancement mode power MOSFET is produced using proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies,audio amplifier, DC motor control, and variable switching power applications.

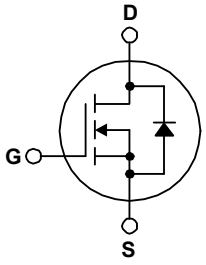


1.G 2.D 3.S

TO-252(DPAK) top view

Features

- V_{DS}(V) = 100V
- I_D =15.6A (V_{GS}= 10V)
- $R_{DS(ON)}$ < 100mΩ (V_{GS} = 10V)
- $R_{DS(ON)}$ < 110mΩ (V_{GS} = 5V)
- Low Gate Charge (Typ. 14 nC)
- Low Crss (Typ. 35 pF)



Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter			FQD19N10LTM	Unit
V_{DSS}	Drain-Source Voltage			100	V
I_D	Drain Current	- Continuous (T_C = 25°C)		15.6	A
		- Continuous (T_C = 100°C)		9.8	A
I_{DM}	Drain Current	- Pulsed	(Note 1)	62.4	A
V_{GSS}	Gate-Source Voltage			± 20	V
E_{AS}	Single Pulsed Avalanche Energy		(Note 2)	220	mJ
I_{AR}	Avalanche Current		(Note 1)	15.6	A
E_{AR}	Repetitive Avalanche Energy		(Note 1)	5.0	mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	6.0	V/ns
P_D	Power Dissipation (T_A = 25°C) *			2.5	W
	Power Dissipation (T_C = 25°C)			50	W
	- Derate Above 25°C			0.4	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range			-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C

Thermal Characteristics

Symbol	Parameter	FQD19N10LTM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	2.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	
	Thermal Resistance, Junction to Ambient (*1 in^2 Pad of 2-oz Copper), Max.	50	

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	100			V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C		0.09		V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 100 V, V_{GS} = 0 V			1	μA
		V_{DS} = 80 V, T_C = 125°C			10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 20 V, V_{DS} = 0 V			100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -20 V, V_{DS} = 0 V			-100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	1.0		2.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 7.8 A V_{GS} = 5 V, I_D = 7.8 A		74 82	100 110	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 30 V, I_D = 7.8 A		14		S
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz		670	870	pF
C_{oss}	Output Capacitance			160	210	pF
C_{rss}	Reverse Transfer Capacitance			35	45	pF
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 50 V, I_D = 19 A, R_G = 25 Ω (Note 4)		14	38	ns
t_r	Turn-On Rise Time			410	830	ns
$t_{d(off)}$	Turn-Off Delay Time			20	50	ns
t_f	Turn-Off Fall Time			140	290	ns
Q_g	Total Gate Charge	V_{DS} = 80 V, I_D = 19 A, V_{GS} = 5 V (Note 4)		14	18	nC
Q_{gs}	Gate-Source Charge			2.9		nC
Q_{gd}	Gate-Drain Charge			9.2		nC
I_S	Maximum Continuous Drain-Source Diode Forward Current				15.6	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current				62.4	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 15.6 A			1.5	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = 19 A, dI_F / dt = 100 A/μs		80		ns
Q_{rr}	Reverse Recovery Charge			0.195		μC

Notes:
1. Repetitive rating : pulse-width limited by maximum junction temperature.
2. L = 1.35 mH, I_{AS} = 15.6 A, V_{DD} = 25 V, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ 19 A, di/dt ≤ 300 A/μs, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C.
4. Essentially independent of operating temperature.

Typical Characteristics

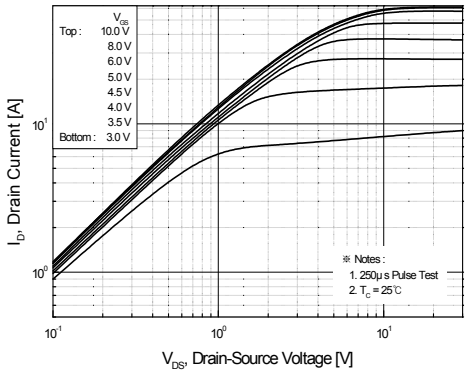


Figure 1. On-Region Characteristics

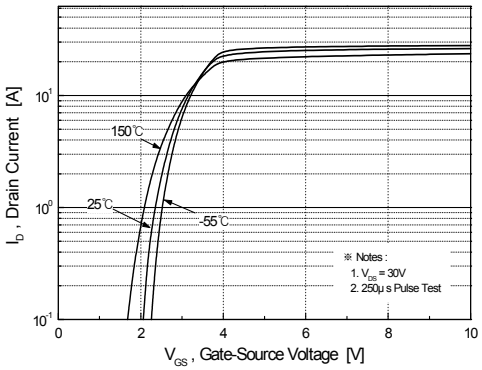


Figure 2. Transfer Characteristics

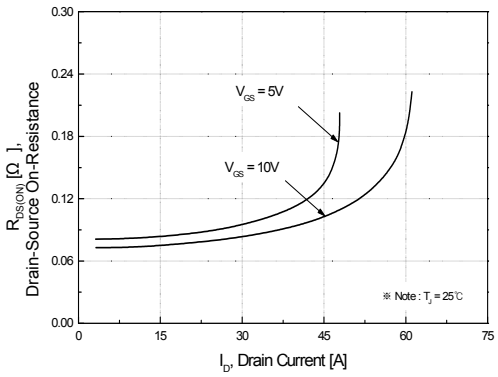


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

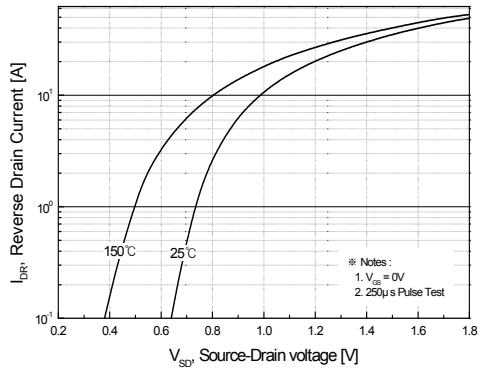


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

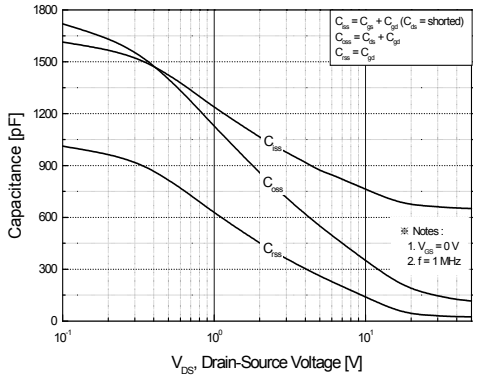


Figure 5. Capacitance Characteristics

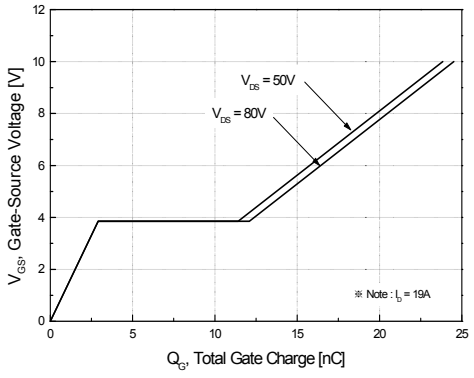


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

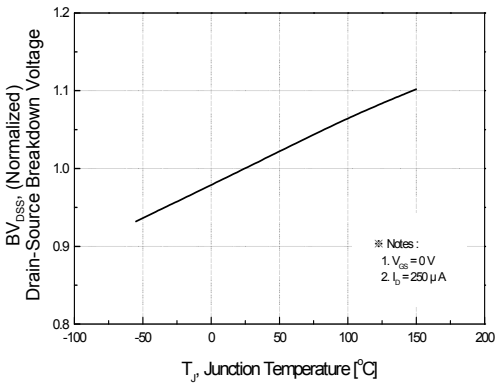


Figure 7. Breakdown Voltage Variation vs. Temperature

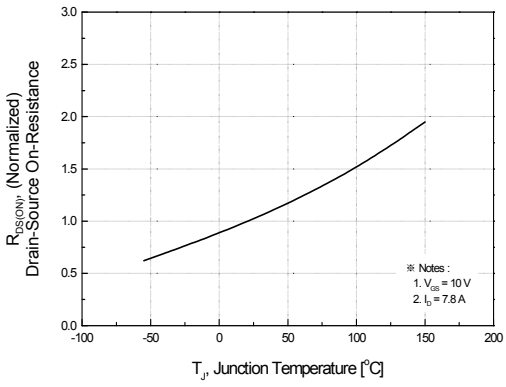


Figure 8. On-Resistance Variation vs. Temperature

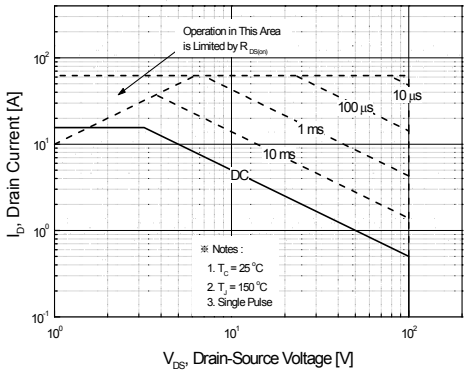


Figure 9. Maximum Safe Operating Area

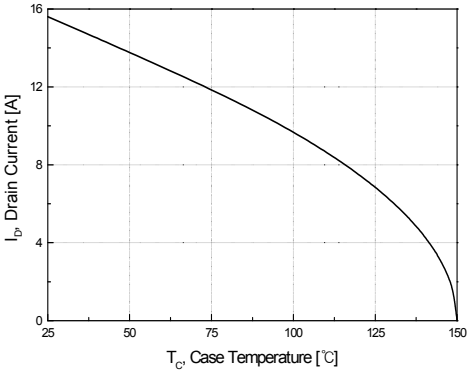


Figure 10. Maximum Drain Current vs. Case Temperature

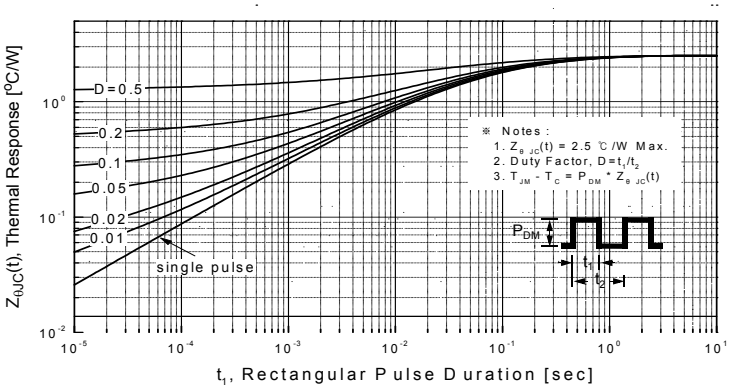
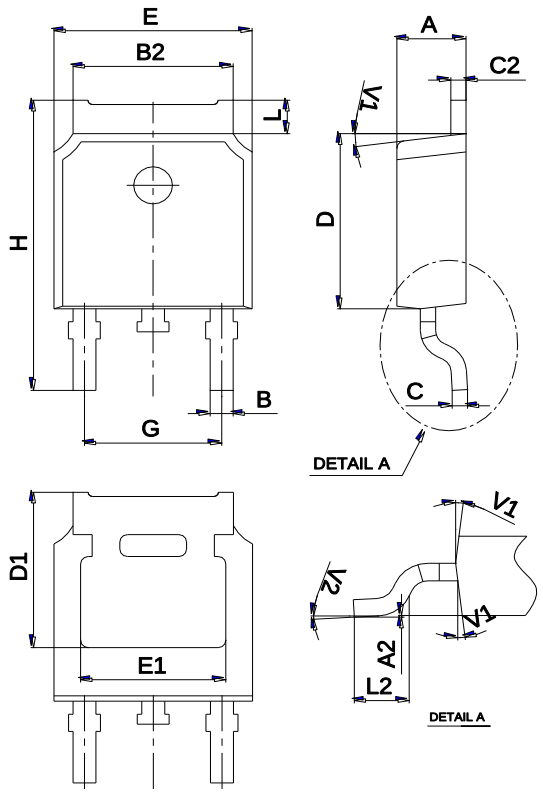


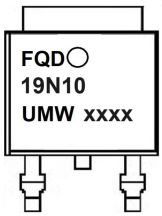
Figure 11. Transient Thermal Response Curve

Package Mechanical Data TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
UMW FQD19N10LTM	TO-252	2500	Tape and reel

单击下面可查看定价，库存，交付和生命周期等信息

>>UMW(友台半导体)